

## Supplementary Information

### Synthesis of 2D NiCo-MOF/GO/CNTs Flexible Films for High-Performance Supercapacitors

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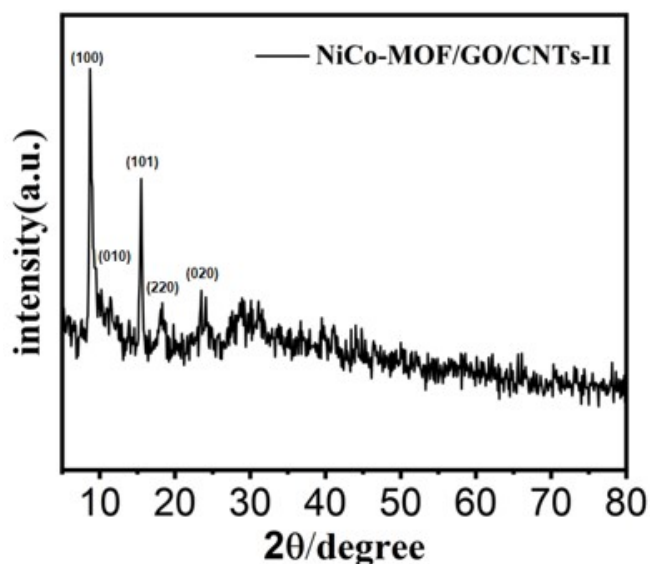


Fig.S1. XRD pattern of NiCo-MOF/GO/CNTs-II

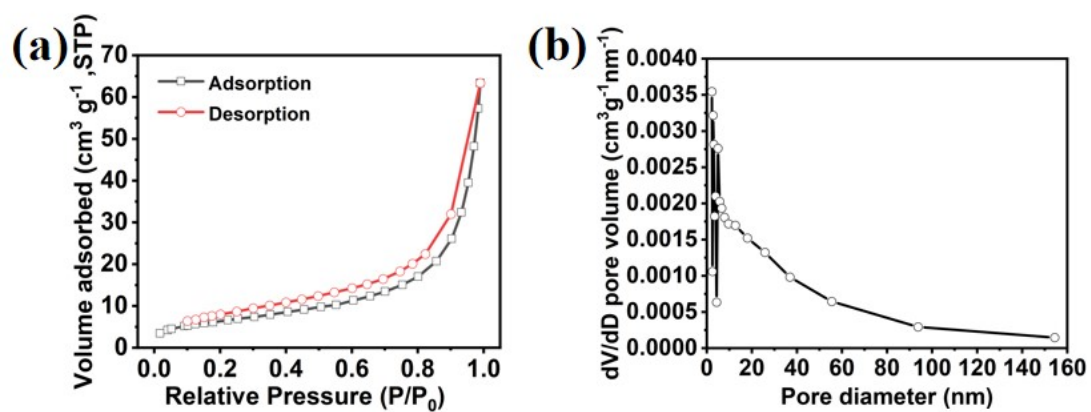


Fig.S2. (a) Nitrogen adsorption-desorption isotherms and (b) pore diameter distribution of NiCo-MOF/GO/CNTs-II



Fig.S3. Contact angle measurement of NiCo-MOF/GO/CNTs-II

The contact Angle of NiCo-MOF/GO/ CNT-II was 33.8°, indicating good wettability.

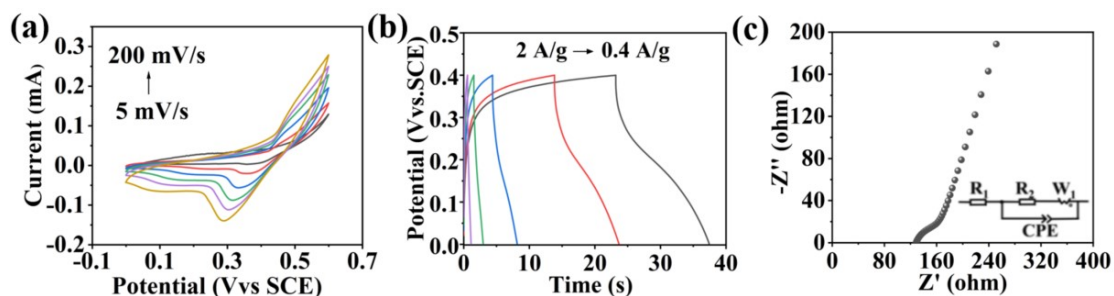


Fig.S4. (a) Cyclic voltammetry (CV) curves at varying scan rates, ranging from 5 to 200  $\text{mV s}^{-1}$  (from inside to outside: 5, 10, 20, 50, 100, and 200  $\text{mV s}^{-1}$ ), (b) GCD curves at different current densities, with current densities presented from left to right as 2, 1, 0.7, 0.5, and 0.4  $\text{A g}^{-1}$  for the bare NiCo-MOF film, and (c) Nyquist plots for bare NiCo-MOF

The calculated specific capacitance of the bare NiCo-MOF film is 14.6, 12.4, 6.6 , 3.7, and 2.7  $\text{F g}^{-1}$  at current densities of 0.4, 0.5, 0.7, 1, and 2  $\text{A g}^{-1}$ , respectively. Upon fitting the data, the equivalent series resistance of the bare NiCo-MOF films is 138  $\Omega$  and the charge transfer resistance is 26  $\Omega$  .

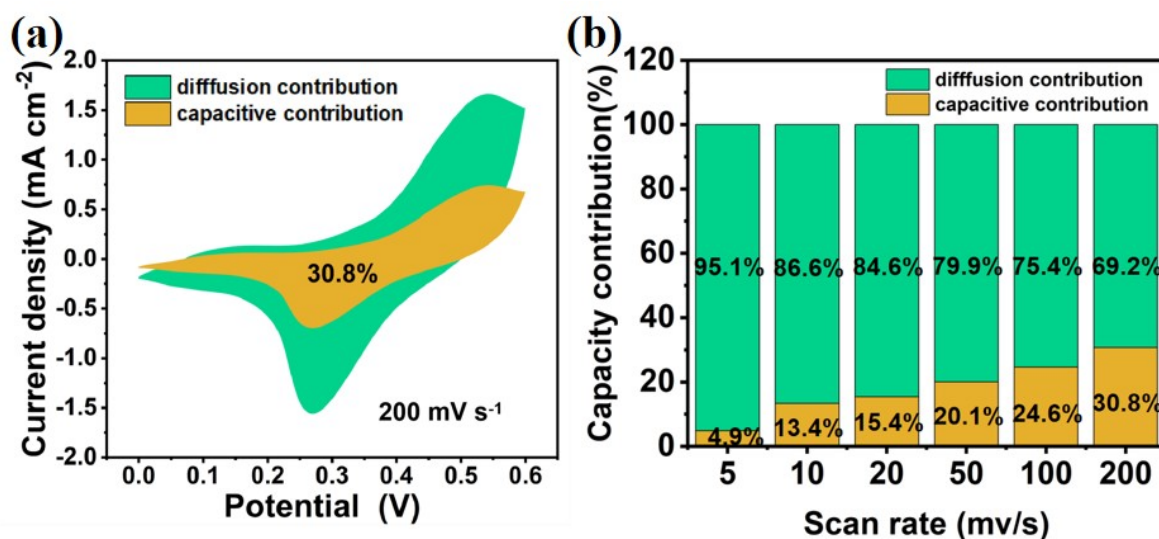


Fig.S5. (a) capacitive and diffusion contribution at 200  $\text{mV s}^{-1}$  for the MOF/GO/CNTs-II electrode and (b) bar graph of the capacitive and diffusion contribution at different scan rates